

Number	Hit#	Search Text	IP	Time Stamp
1	144	hardmask or "hard mask" or SiN or "silicon nitride" same APC or antireflect or "anti reflective coating"	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:10
	144	hardmask or "hard mask" or SiN or "silicon nitride" same APC or antireflect or "anti reflective coating" same etch\$	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:10
	1144	resist or photoresist or pattern or patterned or patterning same APC or antireflect or "anti reflective coating"	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:10
4	144	resist or photoresist or pattern or patterned or patterning with APC or antireflect or "anti reflective coating"	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:10
6	884	resist or photoresist or pattern or patterned or patterning with APC or antireflect or "anti reflective coating" same etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/04/14 10:18
7	192	hardmask or "hard mask" or SiN or "silicon nitride" same resist or photoresist or pattern or patterned or patterning with APC or antireflect or "anti reflective coating" same etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:10
8	127	resist or photoresist or pattern or patterned or patterning with APC or antireflect or "anti reflective coating" same etch\$3 and 488/0.6 mic.	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:10
9	1055	hardmask or "hard mask" or SiN or "silicon nitride" with APC or antireflect or "anti reflective coating"	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:10
9	134	resist or photoresist or pattern or patterned or patterning same hardmask or "hard mask" or SiN or "silicon nitride" with APC or antireflect or "anti reflective coating"	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:10
10	4672	pattern or patterned or patterning with APC or antireflect or "anti reflective coating"	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:52
11	481	pattern or patterned or patterning with APC or antireflect or "anti reflective coating" with opening or via or contact	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:51
12	1209	pattern or patterned or patterning same APC or antireflect or "anti reflective coating" same resist or photoresist	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:53
13	144	pattern or patterned or patterning with APC or antireflect or "anti reflective coating" with resist or photoresist	USPAT; EPO; JPO; IBM_TDB	2003/04/14 10:10
14	144	pattern or patterned or patterning with APC or antireflect or "anti reflective coating" with resist or photoresist and 488/0.6 mic.	USPAT; EPO; JPO; IBM_TDB	2003/04/14 10:10
15	144	opening or contact same APC or antireflect or "anti reflective coating" same BAP	USPAT; EPO; JPO; IBM_TDB	2003/04/14 10:10
15	144	opening or contact with APC or antireflect or "anti reflective coating" same BAP	USPAT; EPO; JPO; IBM_TDB	2003/04/14 10:10
17	144	opening or contact with APC or antireflect or "anti reflective coating" same BAP same etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/04/14 10:10
18	144	opening or contact with polyimide or	USPAT; EPO; JPO; IBM_TDB	2003/04/14 10:10